

P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)			
- 30	0.173 at V _{GS} = - 10 V	- 0.98 ^a	3.25			
	0.243 at V _{GS} = - 4.5 V	- 0.83	3.23			

FEATURES

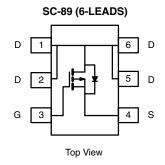
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

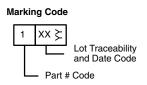


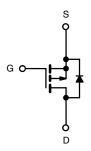
ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

· Load Switch







Ordering Information: Si1073X-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 30			
Gate-Source Voltage		V _{GS}	± 20	V	
	T _A = 25 °C	1	- 0.98 ^{b, c}		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	- 0.78 ^{b, c}		
Pulsed Drain Current		I _{DM}	- 8	Α	
Avalanche Current L = 0.1 mH		I _{AS}	- 6		
Repetitive Avalanche Energy		E _{AS}	1.8	mJ	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.2 ^{b, c}	А	
M ·	T _A = 25 °C	В	0.236 ^{b, c}	W	
Maximum Power Dissipation ^a	T _A = 70 °C	P _D	0.151 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Manifestor Location to Austrianth d	t ≤ 5 s	R _{thJA}	440	530	°C/W		
Maximum Junction-to-Ambient ^{b, d}	Steady State	' 'thJA	540	650	C/VV		

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 650 °C/W.

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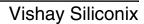


Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = -250 \mu\text{A}$	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		- 30.7			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	- I _D = - 250 μA		3.78		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Oata Wallana Busin Oamant	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	, , , ,	
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 85 °C			- 10 μA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = \ge 5 \text{ V}, V_{GS} = -10 \text{ V}$	- 8			Α	
Durin Course On Chata Benintana	В	V _{GS} = - 10 V, I _D = - 0.98 A		0.144	0.173	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.83 \text{ A}$		0.202	0.243		
Forward Transconductance	9 _{fs}	V _{DS} = - 15 V, I _D = - 0.98 A		3.52		S	
Dynamic ^b							
Input Capacitance	C _{iss}			265			
Output Capacitance	C _{oss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		51		pF	
Reverse Transfer Capacitance	C _{rss}			39			
Total Gate Charge	0	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.98 \text{ A}$		3.25	4.88	nC	
Total date onlinge	₩g	Q _g		6.3	9.45		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -0.98 \text{ A}$		1.02			
Gate-Drain Charge	Q_{gd}			1.47			
Gate Resistance	R_g	f = 1 MHz		14	21	Ω	
Turn-On Delay Time	t _{d(on)}			6	9		
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 19.2 \Omega$		10	15		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -0.78 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		14	21		
Fall Time	t _f			6	9	ne	
Turn-On Delay Time	t _{d(on)}			26	39	ns	
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 22.72 \Omega$		28	42		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 0.66 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		28	42		
Fall Time	t _f			12	18		
Drain-Source Body Diode Characteristi	cs						
Pulse Diode Forward Current ^a	I _{SM}	_			8	Α	
Body Diode Voltage	V_{SD}	I _S = - 0.63 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			14.3	21.45	nC	
Body Diode Reverse Recovery Charge	Q _{rr}	L 0.7 A dl/dt = 100 A/vs		12.16	18.25		
Reverse Recovery Fall Time	t _a	t_a		11.1		ns	
Reverse Recovery Rise Time	t _b			3.2			

Notes:

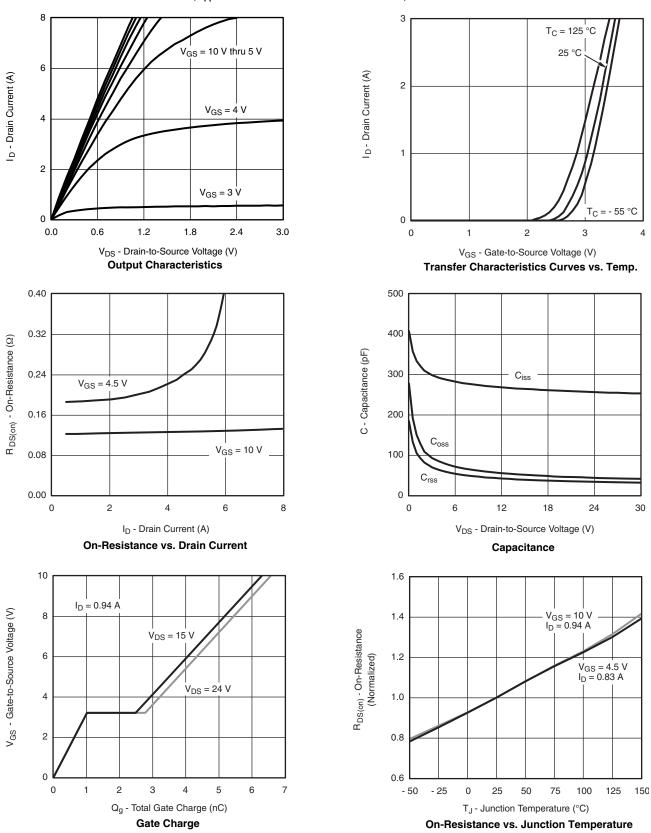
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





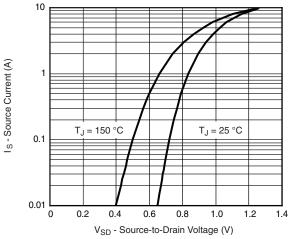
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



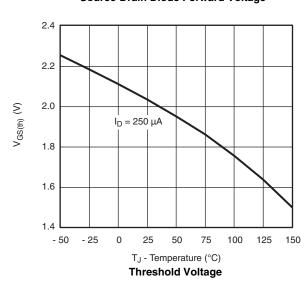
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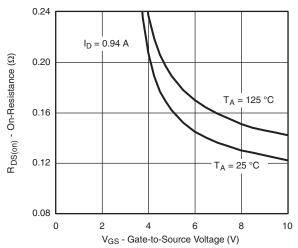
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TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

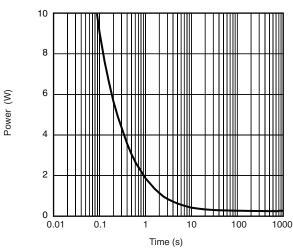




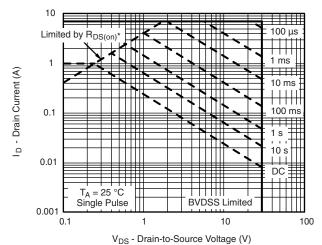




R_{DS(on)} vs. V_{GS} vs. Temperature



Single Pulse Power



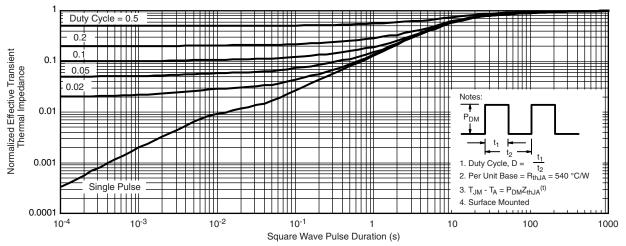
* $V_{GS} > \mbox{ minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient





TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

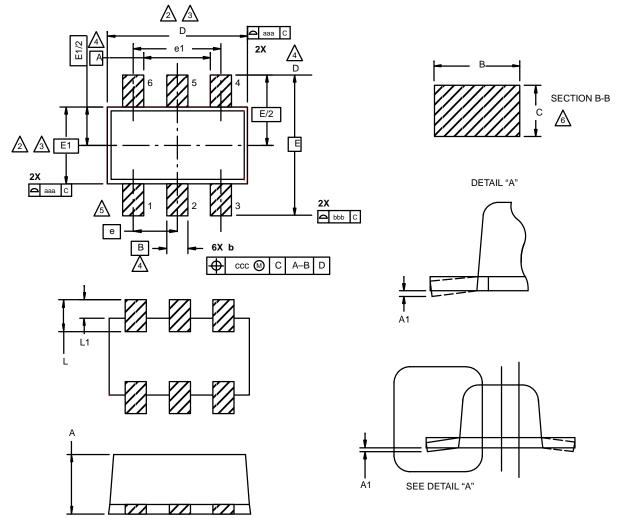


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg274285.



SC89: 6- LEADS (SOT-563F)



NOTES:

1. Dimensions in millimeters.



Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.



Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.



Datums A, B and D to be determined 0.10 mm from the lead tip.



Terminal numbers are shown for reference only.



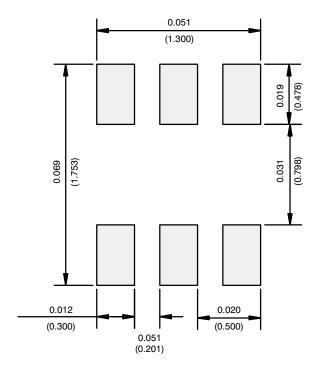
These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

	MILLIMETERS		Tolerances Of Form And					
Dim	Min	Max	Note	Symbol	Position			
Α	0.56	0.60		aaa	0.10			
A1	0.00	0.10		bbb	0.10			
b	0.15	0.30		ccc	0.10			
С	0.10	0.18						
D	1.50	1.70	2, 3					
E	1.55	1.70						
E1	1.20 BSC		2, 3					
е	0.50 BSC							
e1	1.00 BSC							
L	0.35 BSC							
L1	0.20 BSC							

DWG: 5880



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Revision: 02-Oct-12 Document Number: 91000